

# Thyristor \ Diode Module

$$V_{RRM} = 2 \times 800 \text{ V}$$

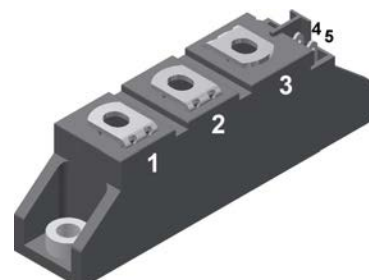
$$I_{TAV} = 60 \text{ A}$$

$$V_T = 1,24 \text{ V}$$

Phase leg

Part number

**MCD56-08io1B**



Backside: isolated

 E72873



## Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

## Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

## Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

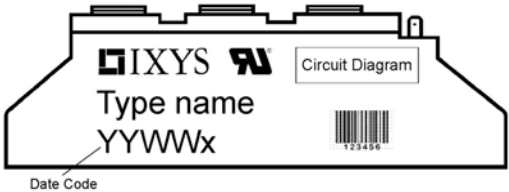
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| Rectifier      |                                                             |                                                                                                                                                                         |                                | Ratings |      |      |                   |
|----------------|-------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------|---------|------|------|-------------------|
| Symbol         | Definition                                                  | Conditions                                                                                                                                                              |                                | min.    | typ. | max. | Unit              |
| $V_{RSM/DSM}$  | <b>max. non-repetitive reverse/forward blocking voltage</b> | $T_{VJ} = 25^{\circ}\text{C}$                                                                                                                                           |                                |         |      | 900  | V                 |
| $V_{RRM/DRM}$  | <b>max. repetitive reverse/forward blocking voltage</b>     | $T_{VJ} = 25^{\circ}\text{C}$                                                                                                                                           |                                |         |      | 800  | V                 |
| $I_{R/D}$      | <b>reverse current, drain current</b>                       | $V_{R/D} = 800\text{ V}$                                                                                                                                                | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 200  | $\mu\text{A}$     |
|                |                                                             | $V_{R/D} = 800\text{ V}$                                                                                                                                                | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 5    | mA                |
| $V_T$          | <b>forward voltage drop</b>                                 | $I_T = 100\text{ A}$                                                                                                                                                    | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 1,26 | V                 |
|                |                                                             | $I_T = 200\text{ A}$                                                                                                                                                    |                                |         |      | 1,57 | V                 |
|                |                                                             | $I_T = 100\text{ A}$                                                                                                                                                    | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 1,24 | V                 |
|                |                                                             | $I_T = 200\text{ A}$                                                                                                                                                    |                                |         |      | 1,62 | V                 |
| $I_{TAV}$      | <b>average forward current</b>                              | $T_C = 85^{\circ}\text{C}$                                                                                                                                              | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 60   | A                 |
| $I_{T(RMS)}$   | <b>RMS forward current</b>                                  | 180° sine                                                                                                                                                               |                                |         |      | 94   | A                 |
| $V_{T0}$       | <b>threshold voltage</b>                                    | } <b>for power loss calculation only</b>                                                                                                                                | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 0,85 | V                 |
| $r_T$          | <b>slope resistance</b>                                     |                                                                                                                                                                         |                                |         |      | 3,7  | m $\Omega$        |
| $R_{thJC}$     | <b>thermal resistance junction to case</b>                  |                                                                                                                                                                         |                                |         |      | 0,45 | K/W               |
| $R_{thCH}$     | <b>thermal resistance case to heatsink</b>                  |                                                                                                                                                                         |                                |         | 0,2  |      | K/W               |
| $P_{tot}$      | <b>total power dissipation</b>                              |                                                                                                                                                                         | $T_C = 25^{\circ}\text{C}$     |         |      | 222  | W                 |
| $I_{TSM}$      | <b>max. forward surge current</b>                           | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                        | $T_{VJ} = 45^{\circ}\text{C}$  |         |      | 1,50 | kA                |
|                |                                                             | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                       | $V_R = 0\text{ V}$             |         |      | 1,62 | kA                |
|                |                                                             | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                        | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 1,28 | kA                |
|                |                                                             | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                       | $V_R = 0\text{ V}$             |         |      | 1,38 | kA                |
| $I^2t$         | <b>value for fusing</b>                                     | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                        | $T_{VJ} = 45^{\circ}\text{C}$  |         |      | 11,3 | kA <sup>2</sup> s |
|                |                                                             | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                       | $V_R = 0\text{ V}$             |         |      | 10,9 | kA <sup>2</sup> s |
|                |                                                             | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                        | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 8,13 | kA <sup>2</sup> s |
|                |                                                             | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                       | $V_R = 0\text{ V}$             |         |      | 7,87 | kA <sup>2</sup> s |
| $C_J$          | <b>junction capacitance</b>                                 | $V_R = 400\text{ V}$ $f = 1\text{ MHz}$                                                                                                                                 | $T_{VJ} = 25^{\circ}\text{C}$  |         | 74   |      | pF                |
| $P_{GM}$       | <b>max. gate power dissipation</b>                          | $t_p = 30\text{ }\mu\text{s}$                                                                                                                                           | $T_C = 125^{\circ}\text{C}$    |         |      | 10   | W                 |
|                |                                                             | $t_p = 300\text{ }\mu\text{s}$                                                                                                                                          |                                |         |      | 5    | W                 |
| $P_{GAV}$      | <b>average gate power dissipation</b>                       |                                                                                                                                                                         |                                |         |      | 0,5  | W                 |
| $(di/dt)_{cr}$ | <b>critical rate of rise of current</b>                     | $T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 150\text{ A}$                                                                                       |                                |         |      | 150  | A/ $\mu\text{s}$  |
|                |                                                             | $t_p = 200\text{ }\mu\text{s}; di_G/dt = 0,45\text{ A}/\mu\text{s};$<br>$I_G = 0,45\text{ A}; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 60\text{ A}$                |                                |         |      | 500  | A/ $\mu\text{s}$  |
| $(dv/dt)_{cr}$ | <b>critical rate of rise of voltage</b>                     | $V_D = \frac{2}{3} V_{DRM}$<br>$R_{GK} = \infty$ ; method 1 (linear voltage rise)                                                                                       | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 1000 | V/ $\mu\text{s}$  |
| $V_{GT}$       | <b>gate trigger voltage</b>                                 | $V_D = 6\text{ V}$                                                                                                                                                      | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 1,5  | V                 |
|                |                                                             |                                                                                                                                                                         | $T_{VJ} = -40^{\circ}\text{C}$ |         |      | 1,6  | V                 |
| $I_{GT}$       | <b>gate trigger current</b>                                 | $V_D = 6\text{ V}$                                                                                                                                                      | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 100  | mA                |
|                |                                                             |                                                                                                                                                                         | $T_{VJ} = -40^{\circ}\text{C}$ |         |      | 200  | mA                |
| $V_{GD}$       | <b>gate non-trigger voltage</b>                             | $V_D = \frac{2}{3} V_{DRM}$                                                                                                                                             | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 0,2  | V                 |
| $I_{GD}$       | <b>gate non-trigger current</b>                             |                                                                                                                                                                         |                                |         |      | 10   | mA                |
| $I_L$          | <b>latching current</b>                                     | $t_p = 10\text{ }\mu\text{s}$                                                                                                                                           | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 450  | mA                |
|                |                                                             | $I_G = 0,45\text{ A}; di_G/dt = 0,45\text{ A}/\mu\text{s}$                                                                                                              |                                |         |      |      |                   |
| $I_H$          | <b>holding current</b>                                      | $V_D = 6\text{ V}$ $R_{GK} = \infty$                                                                                                                                    | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 200  | mA                |
| $t_{gd}$       | <b>gate controlled delay time</b>                           | $V_D = \frac{1}{2} V_{DRM}$                                                                                                                                             | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 2    | $\mu\text{s}$     |
|                |                                                             | $I_G = 0,45\text{ A}; di_G/dt = 0,45\text{ A}/\mu\text{s}$                                                                                                              |                                |         |      |      |                   |
| $t_q$          | <b>turn-off time</b>                                        | $V_R = 100\text{ V}; I_T = 150\text{ A}; V_D = \frac{2}{3} V_{DRM}$<br>$di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 20\text{ V}/\mu\text{s}; t_p = 200\text{ }\mu\text{s}$ | $T_{VJ} = 100^{\circ}\text{C}$ |         | 150  |      | $\mu\text{s}$     |

| Package TO-240AA     |                                                                     |                             |                                         | Ratings |      |      |      |
|----------------------|---------------------------------------------------------------------|-----------------------------|-----------------------------------------|---------|------|------|------|
| Symbol               | Definition                                                          | Conditions                  |                                         | min.    | typ. | max. | Unit |
| I <sub>RMS</sub>     | <i>RMS current</i>                                                  | per terminal                |                                         |         |      | 200  | A    |
| T <sub>VJ</sub>      | <i>virtual junction temperature</i>                                 |                             |                                         | -40     |      | 125  | °C   |
| T <sub>op</sub>      | <i>operation temperature</i>                                        |                             |                                         | -40     |      | 100  | °C   |
| T <sub>stg</sub>     | <i>storage temperature</i>                                          |                             |                                         | -40     |      | 125  | °C   |
| Weight               |                                                                     |                             |                                         |         | 81   |      | g    |
| M <sub>D</sub>       | <i>mounting torque</i>                                              |                             |                                         | 2,5     |      | 4    | Nm   |
| M <sub>T</sub>       | <i>terminal torque</i>                                              |                             |                                         | 2,5     |      | 4    | Nm   |
| d <sub>Spp/App</sub> | <i>creepage distance on surface   striking distance through air</i> | <i>terminal to terminal</i> | 13,0                                    | 9,7     |      |      | mm   |
| d <sub>Spb/Apb</sub> |                                                                     | <i>terminal to backside</i> | 16,0                                    | 16,0    |      |      | mm   |
| V <sub>ISOL</sub>    | <i>isolation voltage</i>                                            | t = 1 second                | 50/60 Hz, RMS; I <sub>ISOL</sub> ≤ 1 mA |         | 4800 |      | V    |
|                      |                                                                     | t = 1 minute                |                                         |         | 4000 |      | V    |



| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCD56-08io1B    | MCD56-08io1B       | Box           | 36       | 476463   |

| Similar Part   | Package     | Voltage class |
|----------------|-------------|---------------|
| MCMA65PD1200TB | TO-240AA-1B | 1200          |
| MCMA85PD1200TB | TO-240AA-1B | 1200          |

Equivalent Circuits for Simulation

\* on die level

$T_{VJ} = 125^{\circ}\text{C}$



Thyristor

$V_{0\text{ max}}$

*threshold voltage*

0,85

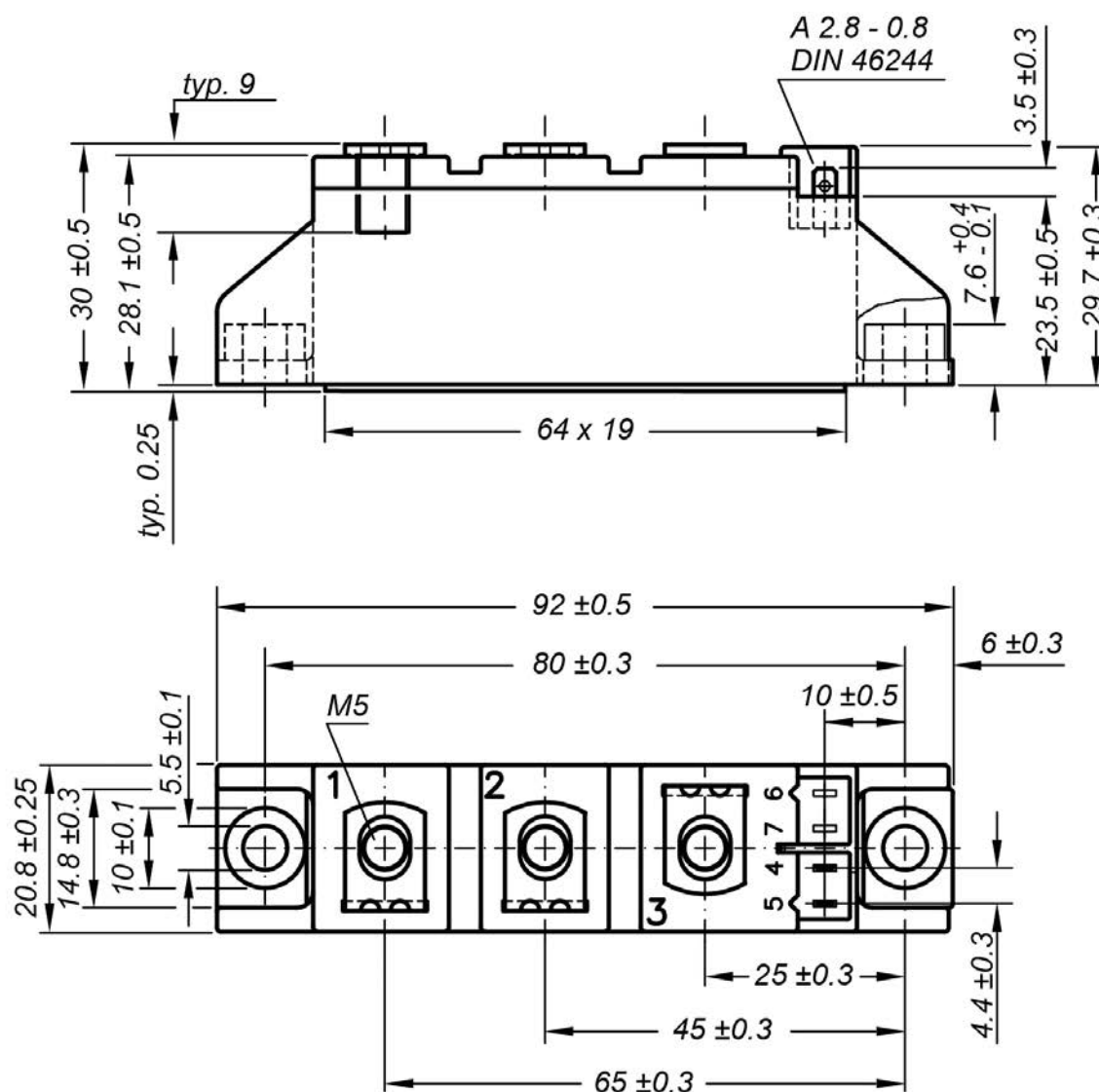
V

$R_{0\text{ max}}$

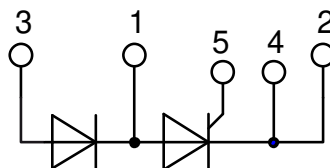
*slope resistance \**

2,5

mΩ



Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red  
Type ZY 200L (L = Left for pin pair 4/5) UL 758, style 3751



## Thyristor

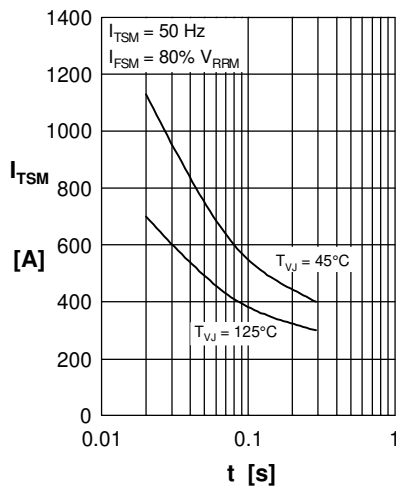


Fig. 1 Surge overload current  $I_{TSM}$ ,  $I_{FSM}$ : Crest value,  $t$ : duration

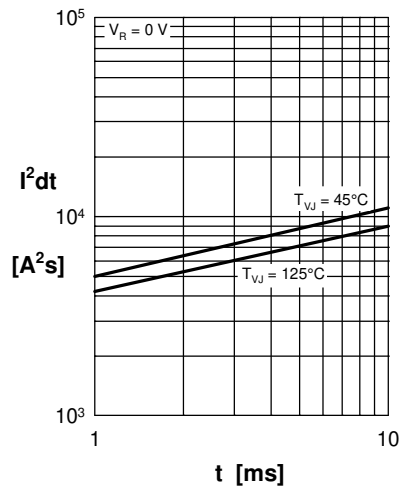


Fig. 2  $I^2dt$  versus time (1-10 ms)

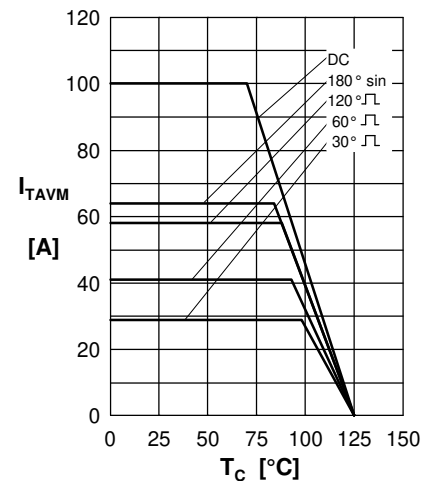


Fig. 3 Max. forward current at case temperature

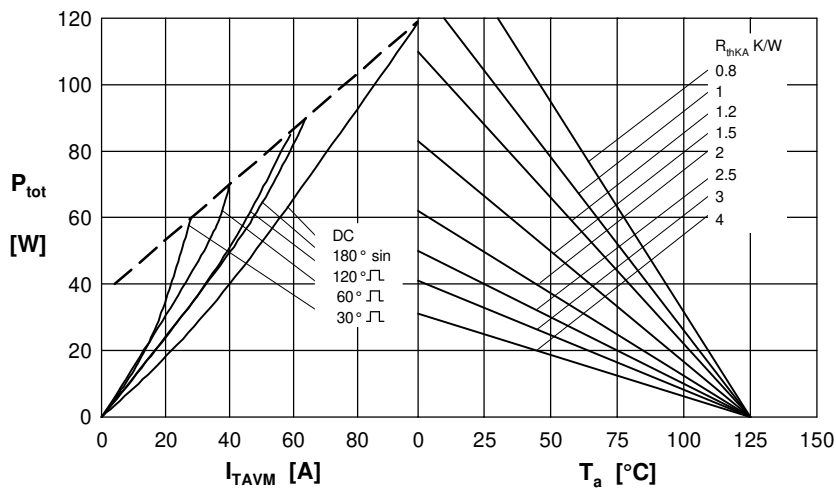


Fig. 4 Power dissipation vs. on-state current & ambient temperature (per thyristor or diode)

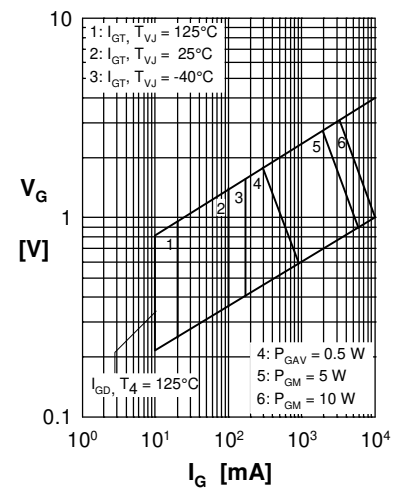


Fig. 5 Gate trigger characteristics

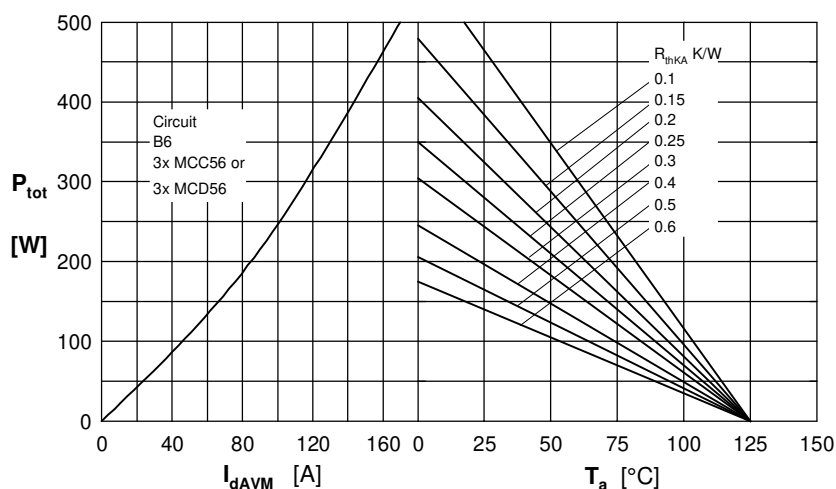


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

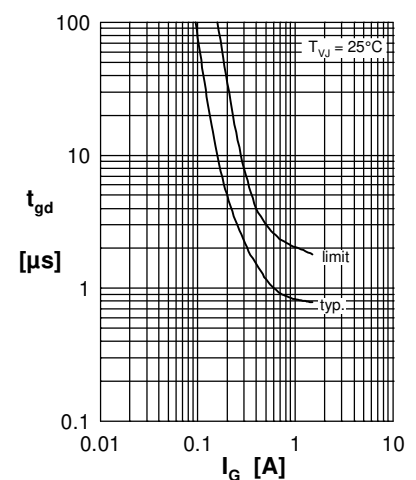


Fig. 7 Gate trigger delay time

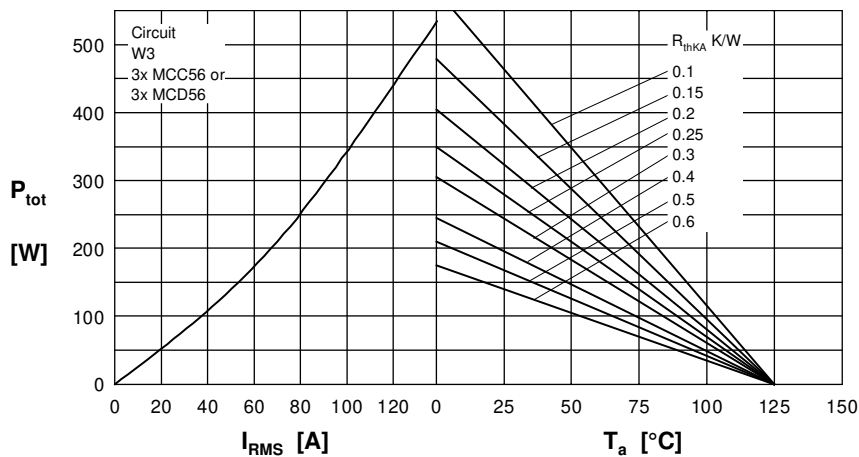
**Rectifier**


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

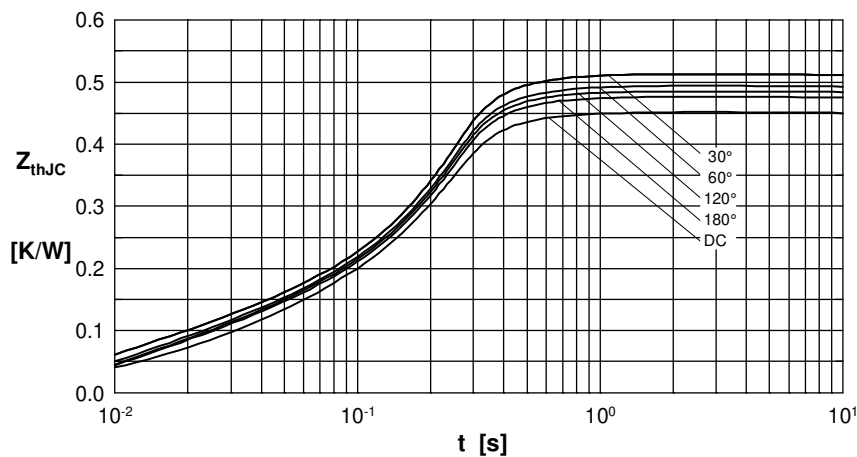


Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)

$R_{thJC}$  for various conduction angles d:

| d    | $R_{thJC}$ [K/W] |
|------|------------------|
| DC   | 0.450            |
| 180° | 0.470            |
| 120° | 0.490            |
| 60°  | 0.505            |
| 30°  | 0.520            |

Constants for  $Z_{thJC}$  calculation:

| i | $R_{thi}$ [K/W] | $t_i$ [s] |
|---|-----------------|-----------|
| 1 | 0.014           | 0.0150    |
| 2 | 0.026           | 0.0095    |
| 3 | 0.410           | 0.1750    |

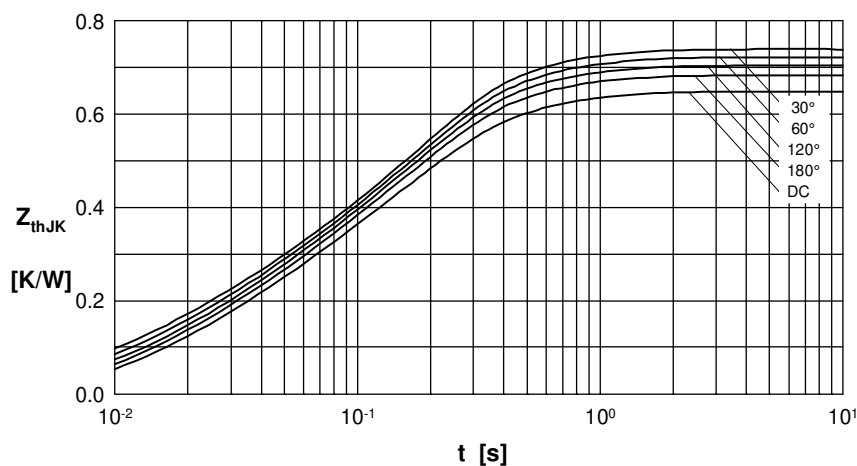


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)

$R_{thJK}$  for various conduction angles d:

| d    | $R_{thJK}$ [K/W] |
|------|------------------|
| DC   | 0.650            |
| 180° | 0.670            |
| 120° | 0.690            |
| 60°  | 0.705            |
| 30°  | 0.720            |

Constants for  $Z_{thJK}$  calculation:

| i | $R_{thi}$ [K/W] | $t_i$ [s] |
|---|-----------------|-----------|
| 1 | 0.014           | 0.0150    |
| 2 | 0.026           | 0.0095    |
| 3 | 0.410           | 0.1750    |
| 4 | 0.200           | 0.6700    |